

MOSFETs Silicon P-Channel MOS (U-MOSVI)

# SSM3J378R

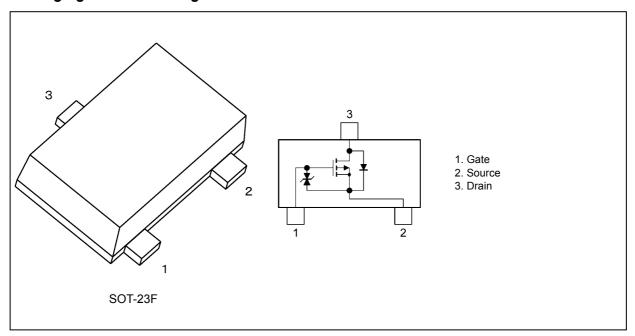
### 1. Applications

• Power Management Switches

#### 2. Features

- (1) AEC-Q101 qualified (Please see the orderable part number list)
- (2) 1.5-V gate drive voltage.
- (3) Low drain-source on-resistance
  - $: R_{DS(ON)} = 88.4 \text{ m}\Omega \text{ (max) (@V_{GS} = -1.5 V)}$
  - $R_{\rm DS(ON)} = 56.0 \text{ m}\Omega \text{ (max) (@V_{\rm GS} = -1.8 V)}$
  - $R_{\rm DS(ON)} = 39.7 \text{ m}\Omega \text{ (max) } (@V_{\rm GS} = -2.5 \text{ V})$
  - $R_{\mathrm{DS(ON)}} = 29.8 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@V_{\mathrm{GS}} = \text{-}4.5 \ \mathrm{V})$

## 3. Packaging and Pin Configuration



#### 4. Orderable part number

| Orderable part number | AEC-Q101 |          | Note           |          |  |
|-----------------------|----------|----------|----------------|----------|--|
| SSM3J378R,LF          | _        |          | General Use    |          |  |
| SSM3J378R,LXGF        | YES      | (Note 1) | Unintended Use | (Note 1) |  |
| SSM3J378R,LXHF        | YES      |          | Automotive Use |          |  |

Note 1: For more information, please contact our sales or use the inquiry form on our website.

Start of commercial production



## 5. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25°C)

| C                      | Characteristics |            | Symbol           | Rating     | Unit |
|------------------------|-----------------|------------|------------------|------------|------|
| Drain-source voltage   |                 |            | V <sub>DSS</sub> | -20        | V    |
| Gate-source voltage    |                 |            | V <sub>GSS</sub> | -8/+6      |      |
| Drain current (DC)     |                 | (Note 1)   | I <sub>D</sub>   | -6.0       | Α    |
| Drain current (pulsed) |                 | (Note 1,2) | I <sub>DP</sub>  | -24.0      |      |
| Power dissipation      |                 | (Note 3)   | P <sub>D</sub>   | 1          | W    |
| Power dissipation      | (t ≤ 10 s)      | (Note 3)   | P <sub>D</sub>   | 2          | W    |
| Channel temperature    |                 |            | T <sub>ch</sub>  | 150        | ℃    |
| Storage temperature    |                 |            | T <sub>stg</sub> | -55 to 150 |      |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150°C.
- Note 2: Pulse width (PW)  $\leq$  10  $\mu$ s, duty  $\leq$  1%
- Note 3: Device mounted on an FR4 board.(25.4 mm × 25.4 mm × 1.6 mm, Cu Pad: 645 mm<sup>2</sup>)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



#### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                |          | Symbol               | Test Condition                                    | Min  | Тур. | Max  | Unit |
|--------------------------------|----------|----------------------|---|------|------|------|------|
| Gate leakage current           |          | I <sub>GSS</sub>     | $V_{GS} = -8/+6 \text{ V}, V_{DS} = 0 \text{ V}$  | _    | _    | ±1   | μА   |
| Drain cut-off current          |          | I <sub>DSS</sub>     | $V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$    | _    | _    | -1   |      |
| Drain-source breakdown voltage |          | V <sub>(BR)DSS</sub> | $I_D$ = -1 mA, $V_{GS}$ = 0 V                     | -20  | _    | _    | ٧    |
| Drain-source breakdown voltage | (Note 1) | V <sub>(BR)DSX</sub> | $I_D$ = -1 mA, $V_{GS}$ = 5 V                     | -15  | _    | _    |      |
| Gate threshold voltage         | (Note 2) | V <sub>th</sub>      | $V_{DS} = -3 \text{ V}, I_{D} = -1 \text{ mA}$    | -0.3 | _    | -1.0 |      |
| Drain-source on-resistance     | (Note 3) | R <sub>DS(ON)</sub>  | $I_D = -3.0 \text{ A}, V_{GS} = -4.5 \text{ V}$   | _    | 24.9 | 29.8 | mΩ   |
|                                |          |                      | $I_D = -2.5 \text{ A}, V_{GS} = -2.5 \text{ V}$   | _    | 31.1 | 39.7 |      |
|                                |          |                      | I <sub>D</sub> = -1.5 A, V <sub>GS</sub> = -1.8 V | _    | 38.8 | 56.0 |      |
|                                |          |                      | I <sub>D</sub> = -0.5 A, V <sub>GS</sub> = -1.5 V | _    | 47.4 | 88.4 |      |
| Forward transfer admittance    | (Note 3) | Y <sub>fs</sub>      | $V_{DS} = -3 \text{ V}, I_{D} = -1.0 \text{ A}$   | 4.5  | 9.1  | _    | S    |

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (-1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

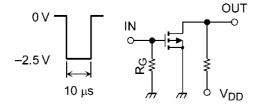
Take this into consideration when using the device.

Note 3: Pulse measurement.

## 6.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub> | $V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$  | _   | 840  | _   | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> | f = 1 MHz  | _   | 99   | _   |      |
| Output capacitance             | Coss             |  | _   | 118  | _   |      |
| Switching time (turn-on time)  | t <sub>on</sub>  | $V_{DD}$ = -10 V, $I_{D}$ = -2.0 A<br>$V_{GS}$ = 0 to -2.5 V, $R_{G}$ = 4.7 $\Omega$ , | _   | 32   | _   | ns   |
| Switching time (turn-off time) | t <sub>off</sub> | Duty $\leq$ 1%, Input: $t_r$ , $t_f$ < 5 ns<br>Common source, See Chapter 6.3          |     | 107  |     |      |

## 6.3. Switching Time Test Circuit



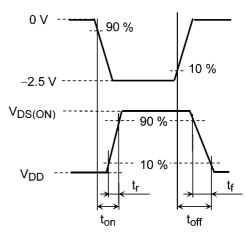


Fig. 6.3.1 Test Circuit of Switching Time

Fig. 6.3.2 Input Waveform/Output Waveform



## 6.4. Gate Charge Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                                 | Symbol           | Test Condition                                     | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | V <sub>DD</sub> = -10 V, V <sub>GS</sub> = -4.5 V, | _   | 12.8 | _   | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> | $I_{D} = -4.0 \text{ A}$                           | _   | 1.4  | _   |      |
| Gate-drain charge                               | Q <sub>gd</sub>  |  | _   | 3.0  | _   |      |

## 6.5. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics       |          | Symbol           | Test Condition                                | Min | Тур. | Max | Unit |
|-----------------------|----------|------------------|---|-----|------|-----|------|
| Diode forward voltage | (Note 1) | V <sub>DSF</sub> | I <sub>D</sub> = 6.0 A, V <sub>GS</sub> = 0 V | _   | 0.87 | 1.2 | V    |

Note 1: Pulse measurement.

## 7. Marking

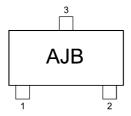


Fig. 7.1 Marking



### 8. Characteristics Curves (Note)

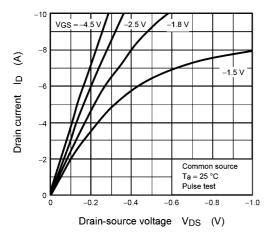


Fig. 8.1 ID - VDS

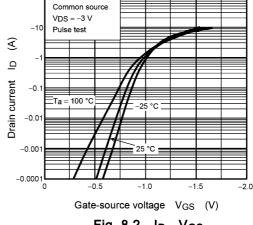


Fig. 8.2 ID - VGS

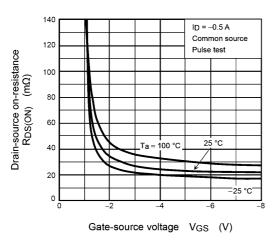


Fig. 8.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

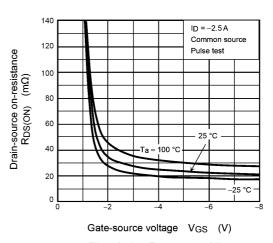


Fig. 8.4 R<sub>DS(ON)</sub> - V<sub>GS</sub>

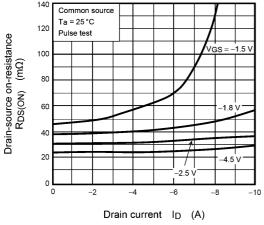


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

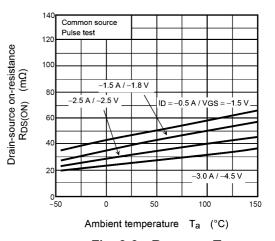


Fig. 8.6 R<sub>DS(ON)</sub> - T<sub>a</sub>



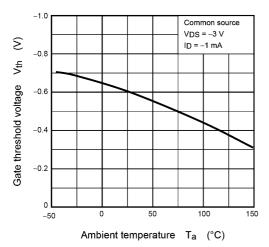
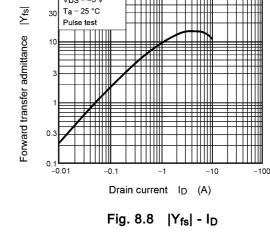


Fig. 8.7 V<sub>th</sub> - T<sub>a</sub>



Common source

VDS = -3 V

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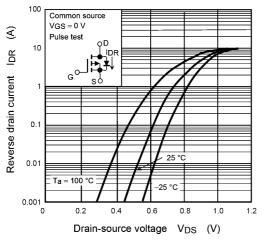


Fig. 8.9 I<sub>DR</sub> - V<sub>DS</sub>

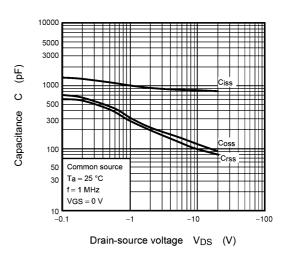


Fig. 8.10 C - V<sub>DS</sub>

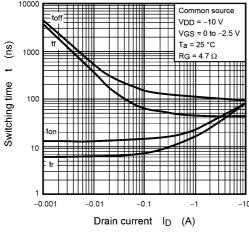


Fig. 8.11 t - I<sub>D</sub>

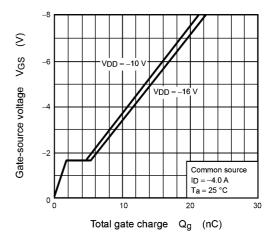
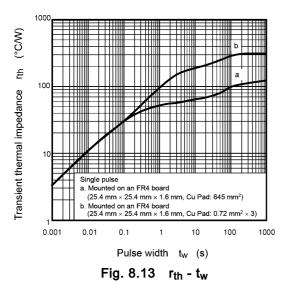


Fig. 8.12 Dynamic Input Characteristics





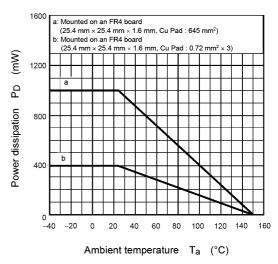


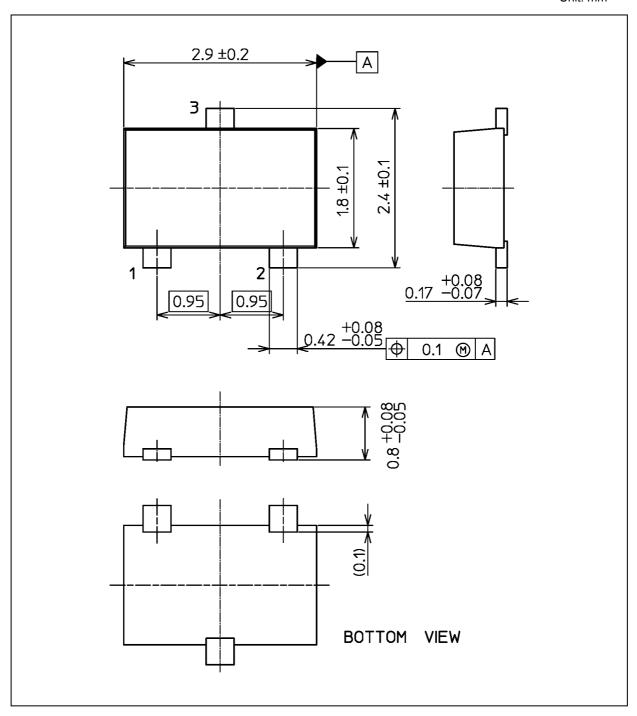
Fig. 8.14 P<sub>D</sub> - T<sub>a</sub>

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 0.011 g (typ.)

|                   | Package Name(s) |
|-------------------|-----------------|
| TOSHIBA: 2-3Z1S   |                 |
| Nickname: SOT-23F |                 |



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